1	Туре	Hits	Search Text	° DBs
1	IS&R	1	("20020063825").PN.	USPAT; US-PGPUB; EPO; JPO
2	BRS	1	rough with (halftone ADJ exposure or two ADJ times ADJ exposure)	USPAT; US-PGPUB; EPO; JPO
3	BRS	2	rough same (halftone ADJ exposure or two ADJ times ADJ exposure)	USPAT; US-PGPUB; EPO; JPO
4	BRS	7	rough and (halftone ADJ exposure or two ADJ times ADJ exposure)	USPAT; US-PGPUB; EPO; JPO
5	BRS	31140	thin ADJ film ADJ transistor TFT	USPAT; US-PGPUB; EPO; JPO
6	BRS	2494	reflect\$3 ADJ electrode	USPAT; US-PGPUB; EPO; JPO
7	BRS	123805	liquid ADJ crystal ADJ display	USPAT; US-PGPUB; EPO; JPO
8	BRS	1187	349/43	USPAT; US-PGPUB; EPO; JPO
9	BRS	70	349/43 and (reflect\$3 ADJ electrode)	USPAT; US-PGPUB; EPO; JPO
10	BRS	497	gate ADJ line with (silicon semiconduct\$3) ADJ layer	USPAT; US-PGPUB; EPO; JPO
11	BRS	418	(liquid ADJ crystal ADJ display) and (gate ADJ line with (silicon semiconduct\$3) ADJ layer)	USPAT; US-PGPUB; EPO; JPO
12	BRS	17952	electrode with reflect\$3	USPAT; US-PGPUB; EPO; JPO
13	BRS	418	(liquid ADJ crystal ADJ display) and (gate ADJ line with (silicon semiconduct\$3) ADJ layer)	USPAT;
14	BRS	96	(electrode with reflect\$3) and ((liquid ADJ crystal ADJ display) and (gate ADJ line	
15	BRS	31140	thin ADJ film ADJ transistor TFT	USPAT; US-PGPUB; EPO; JPO

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	Туре	Hits	Search Text	DBs
16	BRS	6799	(thin ADJ film ADJ transistor TFT) with channel	USPAT; US-PGPUB; EPO; JPO
17	BRS	766	((thin ADJ film ADJ transistor TFT) with channel) and (electrode with reflect\$3)	USPAT; US-PGPUB; EPO; JPO
18	BRS	16198	(capacit\$4 storage) ADJ electrode	USPAT; US-PGPUB; EPO; JPO
19	BRS	182	(((thin ADJ film ADJ transistor TFT) with channel) and (electrode with reflect\$3)) and ((capacit\$4 storage) ADJ electrode)	USPAT; US-PGPUB; EPO; JPO
20	BRS	353	257/348	USPAT; US-PGPUB; ÉPO; JPO
21	BRS	59	(invert\$3 invers\$3) ADJ (thin ADJ film ADJ transistor TFT)	USPAT; US-PGPUB; EPO; JPO
22	BRS	1242	(thin ADJ film ADJ transistor TFT) with invert\$3	USPAT; US-PGPUB; EPO; JPO
23	BRS	1192	349/43	USPAT; US-PGPUB; EPO; JPO
24	BRS	377	((thin ADJ film ADJ transistor TFT) with invert\$3) and gate with top	USPAT; US-PGPUB; EPO; JPO
25	BRS	30	349/43 and (((thin ADJ film ADJ transistor TFT) with invert\$3) and gate with top)	USPAT; US-PGPUB; EPO; JPO
26	BRS	1153	349/43 not ((349/43 and (((thin ADJ film ADJ transistor TFT) with invert\$3) and gate with top)) ((invert\$3 invers\$3) ADJ (thin ADJ film ADJ transistor TFT))	USPAT; US-PGPUB; EPO; JPO
27	BRS	27	(drain source) ADJ electrode with (phosphine PH ADJ 3581660.PN.)	USPAT; US-PGPUB; EPO; JPO
28	IS&R	1	("6081310").PN.	USPAT; US-PGPUB; EPO; JPO
29	BRS	18	reflect\$3 ADJ electrode with ((rough convex concave) and mask)	USPAT; US-PGPUB; EPO; JPO
30	BRS	8	rough and (("1/2" half) ADJ tone ADJ exposure or two ADJ times ADJ exposure)	USPAT; US-PGPUB; EPO; JPO

	Тур	Hits	Search T xt	DBs
31	BRS	:	(convex concave) and (("1/2" half) ADJ tone ADJ exposure or two ADJ times ADJ exposure)	USPAT; US-PGPUB; EPO; JPO
32	BRS	697	349/38	USPAT; US-PGPUB; EPO; JPO

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